

## **Amendments to the Claims**

1. *(Cancelled)*

2. *(Currently Amended)* ~~An amplifier bias circuit as claimed in claim 1;~~ An amplifier bias circuit as claimed in claim 4, wherein the first sensor device is for sensing a lifetime dependent characteristic of the amplifier device.

3. *(Currently Amended)* ~~An amplifier bias circuit as claimed in claim 1;~~ An amplifier bias circuit as claimed in claim 4, wherein the second sensor device is for sensing a temperature dependent characteristic of the amplifier device.

4. *(Currently Amended)* ~~An amplifier bias circuit according to claim 1;~~  
An amplifier bias circuit connectable to an amplifier device, comprising:  
at least one first sensor device for sensing a first amplifier characteristic and for  
providing, at a first sensor output, a bias signal related to the first amplifier characteristic;  
at least one second sensor device for sensing a second amplifier characteristic and  
for providing, at a second sensor output, a bias signal related to the second amplifier  
characteristic;  
which first sensor output and second sensor output are each connectable to at least  
one bias input of said amplifier device; and  
wherein the first sensor device and the second sensor device are communicatively connected to each other and are able to provide each other with a signal related to the sensed characteristic.

5. *(Currently Amended)* ~~An amplifier bias circuit as claimed in claim 1;~~ An amplifier bias circuit as claimed in claim 4, wherein the second sensor device and the first sensor device are connected to each other as a feedback circuit, such that the second sensor output is connected to a first sensor input of the first sensor device and the first sensor output is connected to a second sensor input of the second sensor device.

6. *(Currently Amended)* ~~An amplifier bias circuit as claimed in claim 1;~~ An amplifier bias circuit as claimed in claim 4, wherein the first sensor output and the second sensor output are connected to an RF-decoupling device, which RF-decoupling device is connectable to the bias input.

7. *(Original)* An amplifier bias circuit as claimed in claim 6, wherein the RF-decoupling device comprises a low-pass filter.

8. *(Original)* An amplifier bias circuit as claimed in claim 7, wherein the low-pass filter comprises at least two resistor devices in series and the low-pass filter further comprises a capacitor device connecting a node between the at least two resistor devices to ground.

9. *(Currently Amended)* ~~An amplifier bias circuit according to claim 1;~~ An amplifier bias circuit according to claim 4, wherein the first sensor device comprises a first sensor transistor with at least one voltage input and at least two current outputs, and which voltage input is connected to at least one of the current outputs such that in use the voltage difference between the input and the output connected thereto is small.

10. *(Currently Amended)* ~~An amplifier bias circuit according to claim 1;~~ An amplifier bias circuit according to claim 4, wherein the second sensor device comprises:

a second sensor transistor thermally connectable to the amplifier device, which second sensor transistor has

[[ - ]] at least one voltage input and

[[ - ]] at least two current outputs,

wherein [[ in ]] use a voltage difference between the voltage input and at least one of the current outputs exists.

11. *(Previously Presented)* An amplifier bias circuit as claimed in claim 9, wherein the first sensor transistor is connectable to the amplifier device to form a current mirror circuit.

12. (*Currently Amended*) ~~An amplifier bias circuit according to claim 1;~~ An amplifier bias circuit according to claim 4, wherein at least one of the sensors devices comprises a field effect transistor.

13. (*Currently Amended*) ~~An amplifier bias circuit according to claim 1;~~ An amplifier bias circuit according to claim 4, wherein at least one of the sensor devices comprises an insulated gate field effect transistor.

14. (*Original*) An amplifier bias circuit as claimed in claim 13, wherein at least one of the insulated gate field effect transistors is a laterally diffused metal oxide semiconductor field effect transistor.

15. (*Currently Amended*) ~~An amplifier bias circuit according to claim 1;~~ An amplifier bias circuit according to claim 4, wherein the amplifier bias circuit and the amplifier device are implemented on a single integrated circuit.

16. (*Currently Amended*) ~~An amplifier bias circuit according to claim 1;~~ An amplifier bias circuit according to claim 4, wherein at least one of the sensor devices has at least one characteristic which corresponds to at least one of said amplifier characteristics.

17. (*Cancelled*)

18. (*Currently Amended*) An integrated circuit comprising an amplifier device which is connected to at least one amplifier bias circuit, the amplifier bias circuit comprising:  
[[ - ]] at least one first sensor device for sensing a first amplifier characteristic and for providing at a first sensor output a bias signal related to the first amplifier characteristic;  
[[ - ]] at least one second sensor device for sensing a second amplifier characteristic and for providing at a second sensor output a bias signal related to the second amplifier characteristic;

which first sensor output and second sensor output are each connectable to at least one bias input of ~~said amplifier device;~~ said amplifier device, and

wherein the first sensor device and the second sensor device are communicatively connected to each other and are able to provide each other with a signal related to the sensed characteristic.

19. *(Original)* An integrated circuit as claimed in claim 18 wherein the integrated circuit is a single crystal integrated circuit.

20. *(Currently Amended)* Apparatus comprising an amplifier bias circuit connectable to an amplifier device, the amplifier bias circuit comprising:

- at least one first sensor device for sensing a first amplifier characteristic and for providing at a first sensor output a bias signal related to the first amplifier characteristic;
- at least one second sensor device for sensing a second amplifier characteristic and for providing at a second sensor output a bias signal related to the second amplifier characteristic;

which first sensor output and second sensor output are each connectable to at least one bias input of ~~said amplifier device~~; said amplifier device, and

wherein the first sensor device and the second sensor device are communicatively connected to each other and are able to provide each other with a signal related to the sensed characteristic.